

BAT46WJ Single Schottky barrier diode Rev. 2 – 8 November 2011

Product data sheet

1. Product profile

1.1 General description

Single planar Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a very small and flat lead SOD323F (SC-90) Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Low forward voltage
- Reverse voltage $V_R \le 100 \text{ V}$
- Very small and flat lead SMD plastic package

1.3 Applications

- High-speed switching
- Line termination

1.4 Quick reference data

- Low capacitance
- AEC-Q101 qualified
- Voltage clamping
- Reverse polarity protection

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _R	reverse voltage		-	-	100	V
V _F	forward voltage	I _F = 250 mA	<u>[1]</u> _	-	850	mV
I _R	reverse current	V _R = 75 V	<u>[1]</u> _	-	4	μA
I _R	reverse current	V _R = 75 V	<u>[1]</u> _	-	4	

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2. Pinning information

	Graphic symbol
[1]	
	1 🕂 2

[1] The marking bar indicates the cathode.



3. Ordering information

Table 3. Order	ring informa	ation	
Type number	Package		
	Name	Description	Version
BAT46WJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F

4. Marking

Table 4. Marking codes	
Type number	Marking code
BAT46WJ	JK

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _R	reverse voltage		-	100	V
I _F	forward current		-	250	mA
I _{FSM}	non-repetitive peak forward current	square wave; t _p < 10 ms	<u>[1]</u> -	2.5	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[2][4]	400	mW
			[3][4]	715	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] $T_j = 25 \ ^{\circ}C$ before surge.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[4] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	<u>[1][3]</u> _	-	310	K/W
	junction to ambient		[2][3]	-	175	K/W

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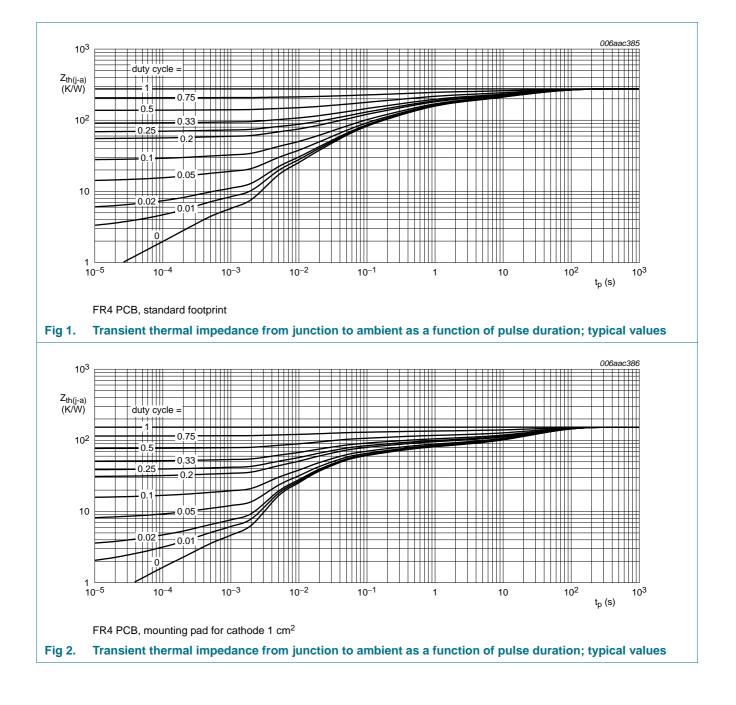
Table 6. Thermal characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[4]</u> _	-	35	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

- [3] Reflow soldering is the only recommended soldering method.
- [4] Soldering point of cathode tab.



7. Characteristics

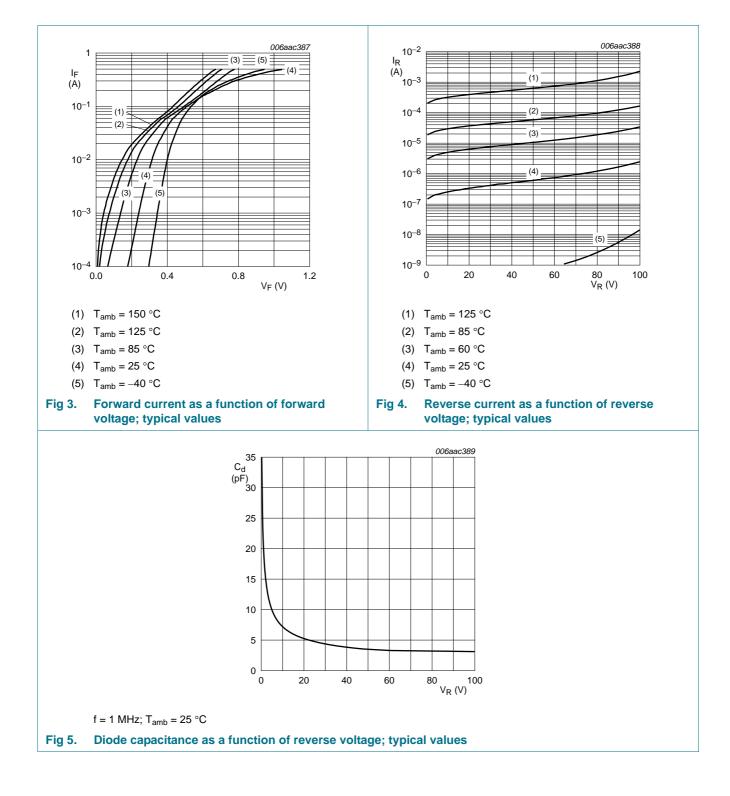
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage		<u>[1]</u>			
		I _F = 0.1 mA	-	175	200	mV
		I _F = 10 mA	-	315	350	mV
		$I_F = 10 \text{ mA}; T_j = -40 ^{\circ}\text{C}$	-	-	470	mV
		I _F = 50 mA	-	415	475	mV
		$I_F = 50 \text{ mA}; T_j = -40 ^{\circ}\text{C}$	-	-	560	mV
		I _F = 250 mA	-	710	850	mV
I _R	reverse current		<u>[1]</u>			
		V _R = 1.5 V	-	0.2	0.5	μA
		V_R = 1.5 V; T_j = 60 °C	-	-	12	μA
		V _R = 10 V	-	0.3	0.8	μA
		V_R = 10 V; T_j = 60 °C	-	-	20	μA
		V _R = 50 V	-	0.7	2	μA
		V_R = 50 V; T_j = 60 °C	-	-	44	μA
		V _R = 75 V	-	1	4	μA
		V_R = 75 V; T_j = 60 °C	-	-	80	μA
		V _R = 100 V	-	2	9	μA
		$V_R = 100 \text{ V}; \text{ T}_j = 60 ^{\circ}\text{C}$	-	-	120	μA
		V_R = 100 V; T_j = 85 °C	-	-	600	μA
C _d	diode capacitance	f = 1 MHz				
		V _R = 0 V	-	-	39	pF
		V _R = 1 V	-	-	21	pF
t _{rr}	reverse recovery time		[2] _	5.9	-	ns

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[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

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Single Schottky barrier diode

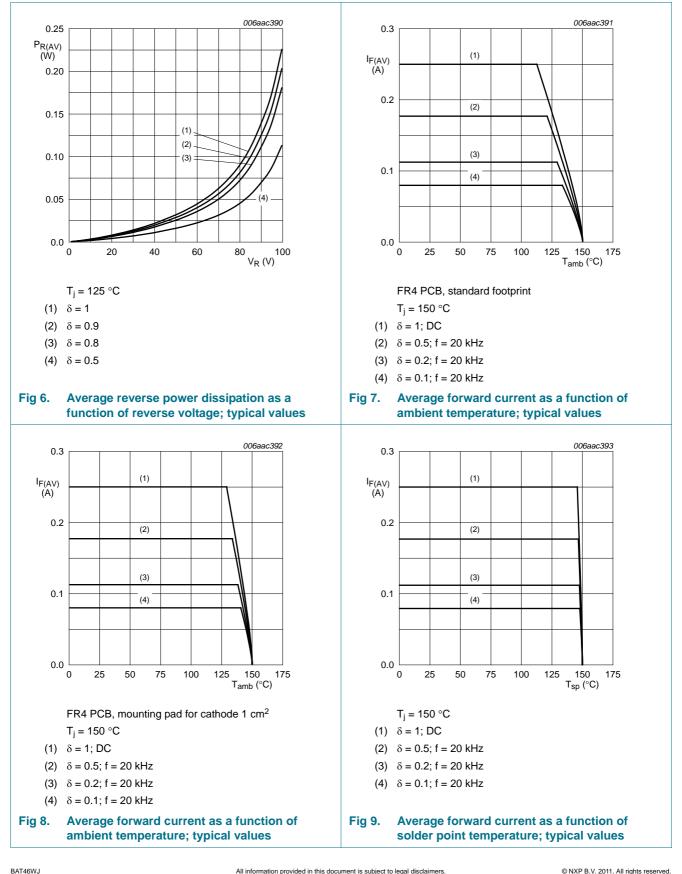


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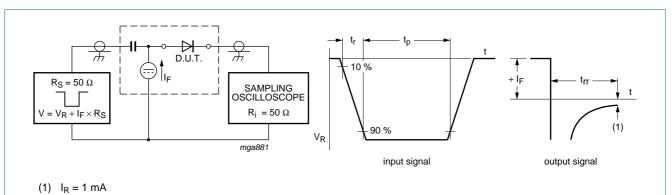
Single Schottky barrier diode



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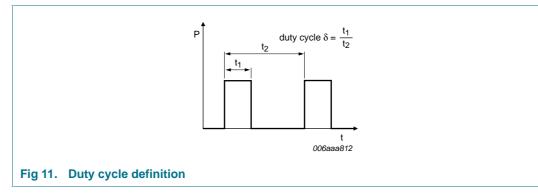
Single Schottky barrier diode

8. Test information



Input signal: reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 100 ns; duty cycle δ = 0.05 Oscilloscope: rise time t_r = 0.35 ns

Fig 10. Reverse recovery time test circuit and waveforms



The current ratings for the typical waveforms as shown in Figure 7, 8 and 9 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

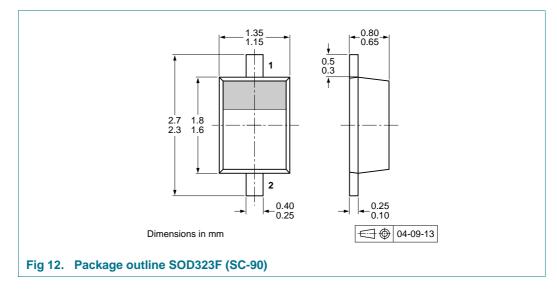
 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Single Schottky barrier diode

9. Package outline



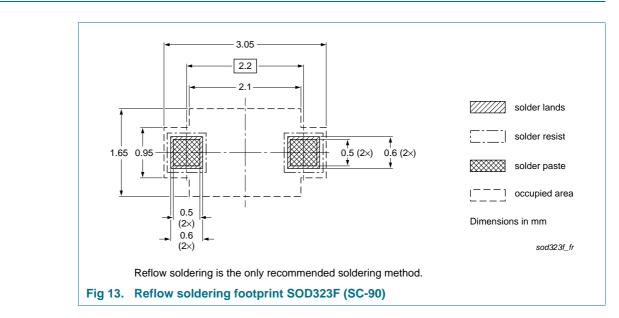
10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			3000	10000
BAT46WJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see <u>Section 14</u>.



11. Soldering

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12. Revision history

Release date	Data sheet status	Change notice	Supersedes
20111108	Product data sheet	-	BAT46WJ v.1
• <u>Table 7</u> : uni	t for reverse current I _R at V	$_{\rm R}$ = 50 V corrected to μ A	١
• <u>Table 7</u> : cor	nditions of reverse voltage	√ _R corrected	
Section 13 f	Legal information": update	d	
20100728	Product data sheet	_	-
	20111108 • <u>Table 7</u> : uni • <u>Table 7</u> : cor • <u>Section 13</u>	20111108 Product data sheet • Table 7: unit for reverse current I _R at V • Table 7: conditions of reverse voltage V • Section 13 "Legal information": update	20111108Product data sheet-• Table 7: unit for reverse current I_R at $V_R = 50$ V corrected to μA • Table 7: conditions of reverse voltage V_R corrected• Section 13 "Legal information": updated

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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